**Product data sheet** 

# 1. General description

Passivated, sensitive gate thyristors in a plastic envelope, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### 2. Features and benefits

- · Sensitive gate
- Planar passivated for voltage ruggedness and reliability
- · Direct triggering from low power drivers and logic ICs
- Surface mountable package

# 3. Applications

- · General purpose switching and phase control
- · Ignition circuits, CDI for 2- and 3-wheelers
- Motor control e.g. small kitchen appliances

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage			-	-	600	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>mb</sub> ≤ 111 °C; <u>Fig. 1</u>		-	-	5	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; $T_{mb} \le 111 ^{\circ}C$ ; Fig. 2; Fig. 3		-	-	8	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>		-	-	75	Α
		half sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 8.3 \text{ ms}$		-	-	82	Α
T <sub>j</sub>	junction temperature		[1]	-	-	125	°C
Static characte	eristics						
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 7$		-	50	200	μΑ
Dynamic chara	ateristics						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; $R_{GK}$ = 100 Ω; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; Fig. 12		50	100	-	V/µs

[1] Operation above 110°C may require the use of a gate to cathode resistor of  $1k\Omega$  or less.

# 5. Pinning information

**Table 2. Pinning information** 

	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	A <del>-                                   </del>
2	A	anode		Ġ sym037
3	G	gate		Symosi
mb	Α	mounting base; connected to anode	1 2 3 IPAK (TO-251)	

# 6. Ordering information

**Table 3. Ordering information** 

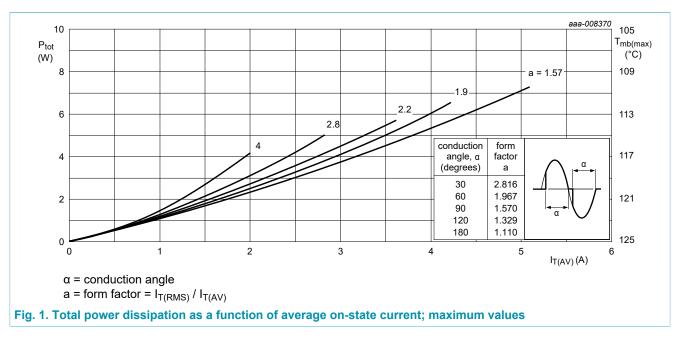
Type number	Package					
	Name	Description	Version			
BT258U-600R	IPAK	plastic single-ended package (IPAK); 3 leads (in-line)	TO-251			

# 7. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage			-	600	V
$V_{RRM}$	repetitive peak reverse voltage			-	600	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>mb</sub> ≤ 111 °C; <u>Fig. 1</u>		-	5	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; $T_{mb} \le 111 ^{\circ}\text{C}$ ; Fig. 2; Fig. 3		-	8	А
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; Fig. 4; Fig. 5		-	75	А
		half sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 8.3  ms$		-	82	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN		-	28	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 1 mA		-	50	A/µs
I <sub>GM</sub>	peak gate current			-	2	Α
$V_{RGM}$	peak reverse gate voltage			-	5	V
$P_{GM}$	peak gate power			-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.5	W
T <sub>stg</sub>	storage temperature			-40	150	°C
Tj	junction temperature		[1]	-	125	°C

[1] Operation above 110°C may require the use of a gate to cathode resistor of  $1k\Omega$  or less.



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### **Logic level thyristor**

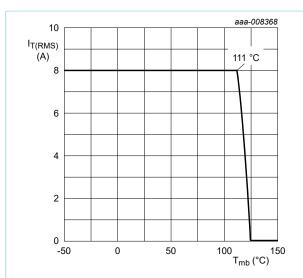


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

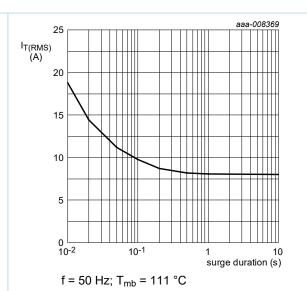


Fig. 3. RMS on-state current as a function of surge duration; maximum values

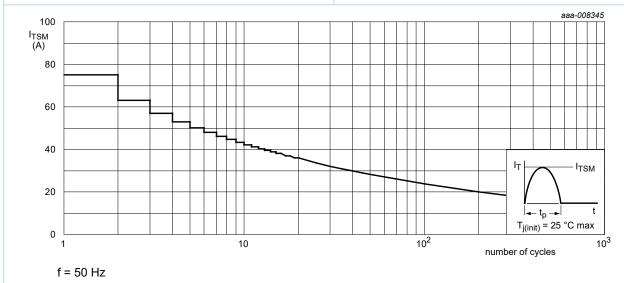
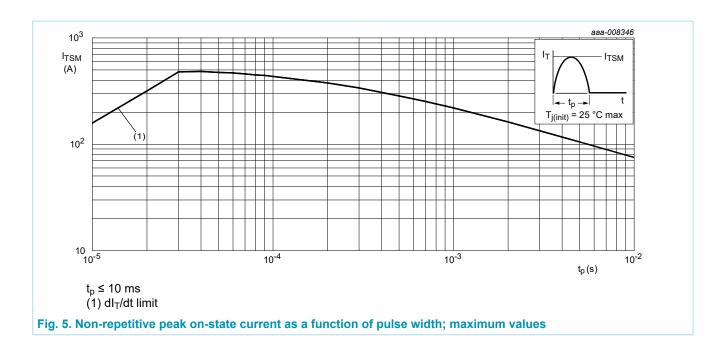


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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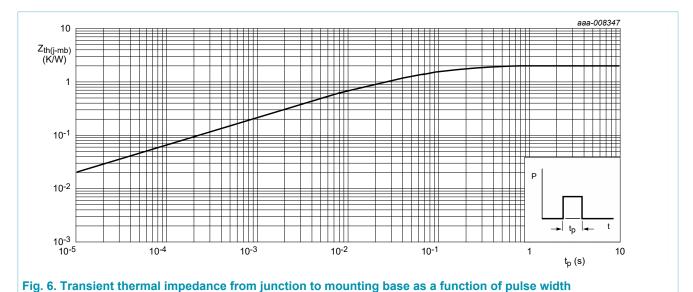
### **Logic level thyristor**



### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 6	-	-	2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	70	-	K/W



## 9. Characteristics

**Table 6. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics		'			
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$	-	50	200	μA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 8$	-	0.4	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	0.3	6	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 16 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.4	1	V
		$V_D = 600 \text{ V}; I_T = 0.1 \text{ A}; T_j = 110 ^{\circ}\text{C};$ Fig. 11	0.1	0.2	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic c	harateristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; $R_{GK}$ = 100 Ω; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; Fig. 12	50	100	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 10 A; $V_D$ = 600 V; $I_G$ = 5 mA; $dI_G/$ dt = 0.2 A/µs; $T_j$ = 25 °C	-	2	-	μs
t <sub>q</sub>	commutated turn-off time	$V_{DM} = 402 \text{ V}; T_j = 125 \text{ °C}; I_{TM} = 12 \text{ A}; V_R = 24 \text{ V}; (dI_T/dt)_M = 10 \text{ A/µs; } dV_D/dt = 2 \text{ V/µs; } R_{GK(ext)} = 1 \text{ k}\Omega; (V_{DM} = 67\% \text{ of } V_{DRM})$	-	100	-	μs

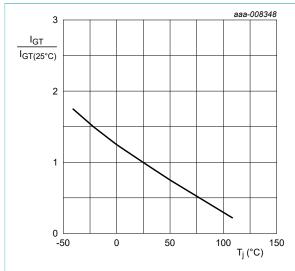


Fig. 7. Normalized gate trigger current as a function of junction temperature

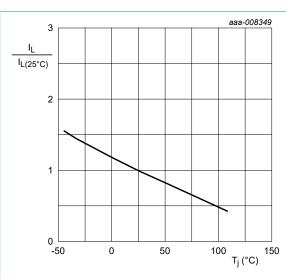


Fig. 8. Normalized latching current as a function of junction temperature

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### Logic level thyristor

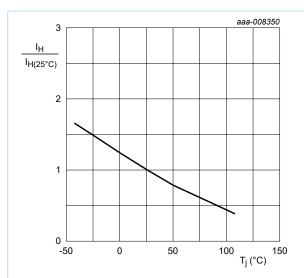
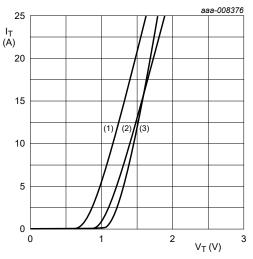


Fig. 9. Normalized holding current as a function of junction temperature



 $V_o = 1.0 \text{ V}; R_s = 0.04 \Omega$ 

(1)  $T_j = 125$  °C; typical values (2)  $T_j = 125$  °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

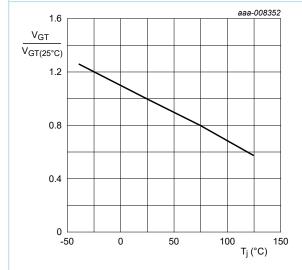


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

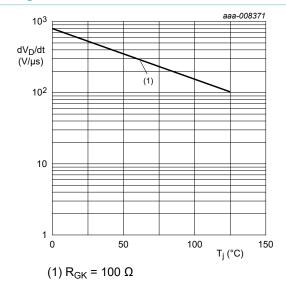
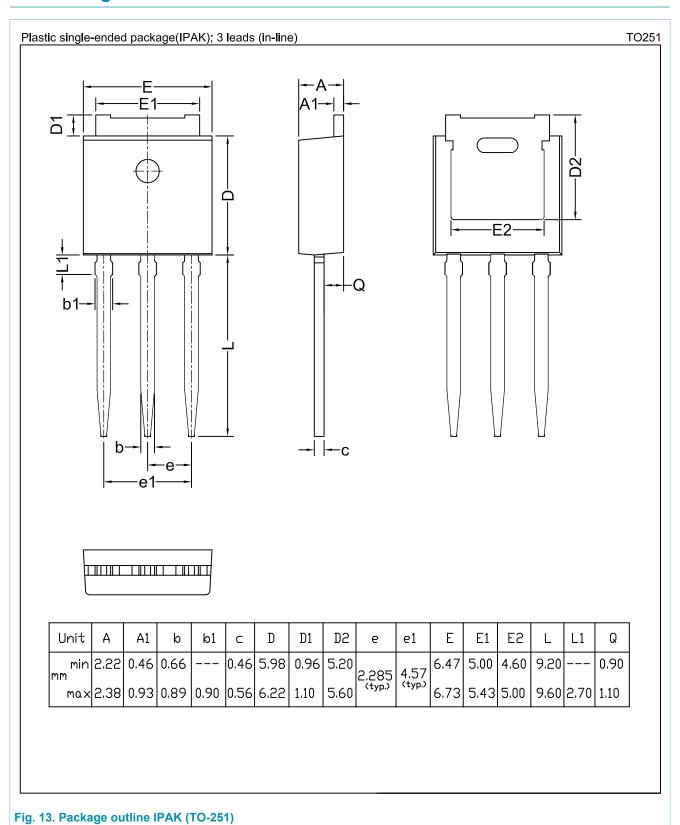


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

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# 10. Package outline



# 11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**Logic level thyristor** 

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# BT258U-600R

**Logic level thyristor** 

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